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Optimization and implementation of a multi-level buck converter for standard CMOS on-chip integration

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Outline

- Introduction and motivation
- Series-connected multiphase multilevel buck converter
 - Ideal topology. Amplifier and regulator operation
 - Self-driven low-floating-capacitor PFM-operated 3-level converter
- Design-space optimization
- Mixed-signal implementation in 0.25µm TSMC CMOS
 - Air-core bondingwire-based inductor, tapered buffer and transistor design
 - Inductor current zero-crossing detection circuit
- Conclusions





Outline

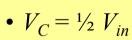
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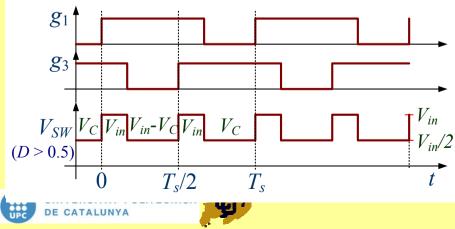


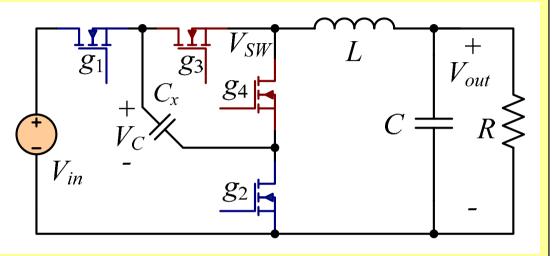


3-Level (2-cell) Buck Converter

- 3-level (2-cell) converter has been proposed for high voltage inverters [Meynard et al., 1992]
- " g_1 - g_2 " & " g_3 - g_4 " are complementary switches
- g₁ and g₃ have the same duty cycle



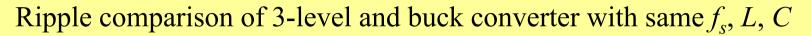


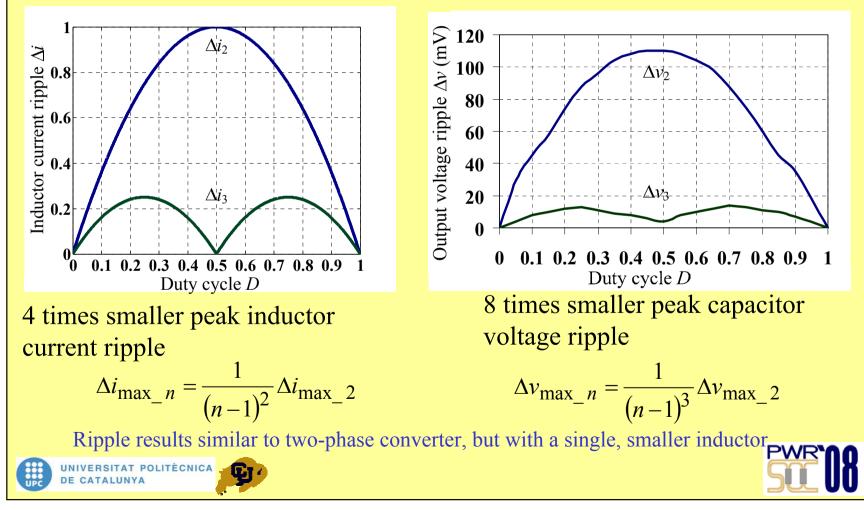


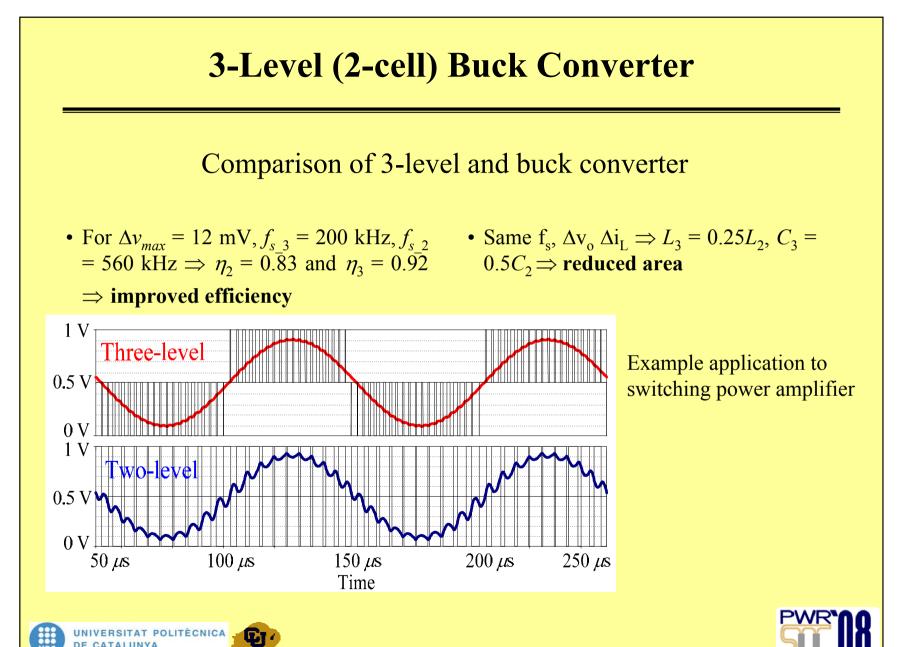
• <u>Objective:</u>

Investigate potential for lower ripple/ higher efficiency / lower reactive component size / higher bandwidth realization of DC-DC converter

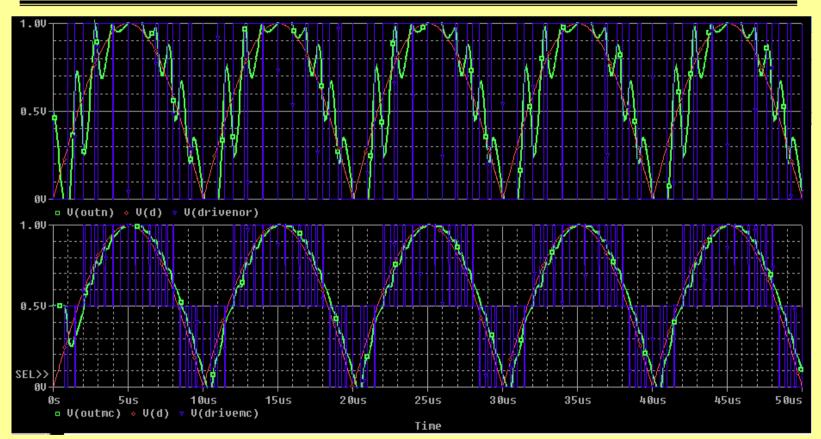
Switching Ripple in the 3-Level Buck Converter







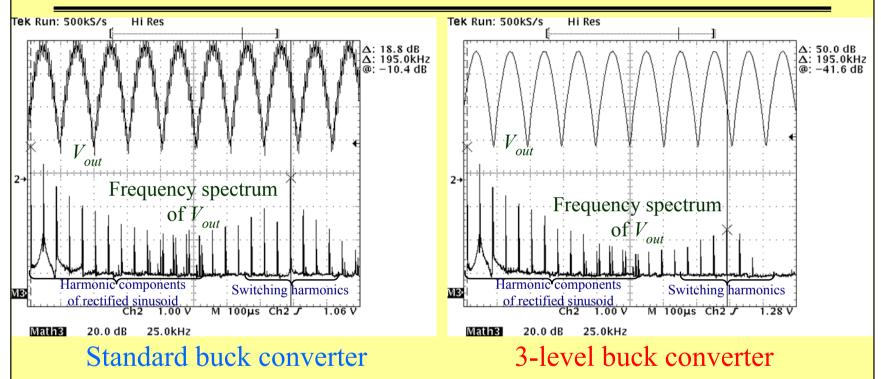
Two-Tone Signal Generation Using a 3-Level and a Buck Converter



A two-tone signal generated with a three-level and a buck converter.

Switching frequency, f_s = 1MHz, f_{sig} = 100kHz, f_o = 550kHz,

Experimental Envelope Tracking Waveforms



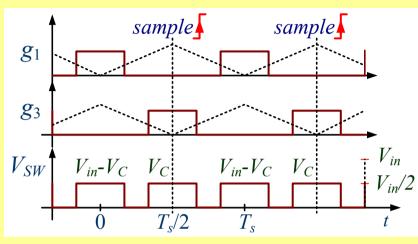
- Standard buck and 3-level buck compared for the same open-loop bandwidth and the same switching frequency
- Modulation: rectified sine-wave at $f_m = 20 \text{ kHz}$
- 30dB lower switching-frequency harmonic in the 3-level converter



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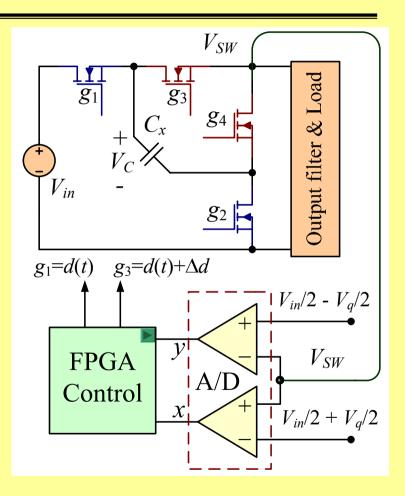


Flying capacitor voltage control



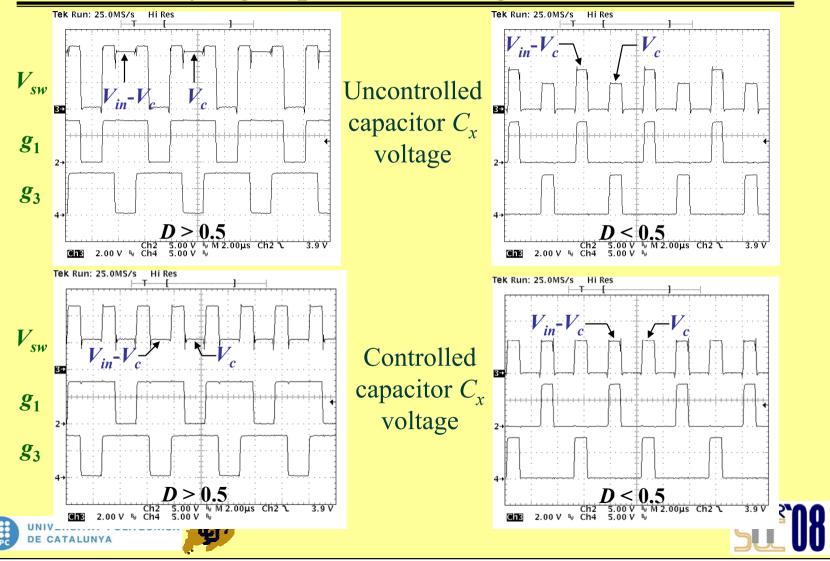
- Digital (verilog) controller implementation using FPGA
- x and y are sampled at $V_{sw} = V_C$ or $V_{sw} = V_{in} - V_C$







Experimental waveforms for flying capacitor voltage control



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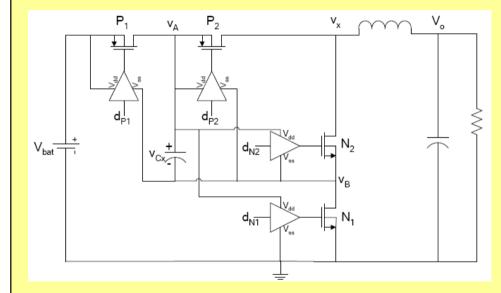
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3-level self-driving PFM low-Cx buck converter

Low-C_x resonant 3-level buck converter in DCM. Self-driving transistor-level topology



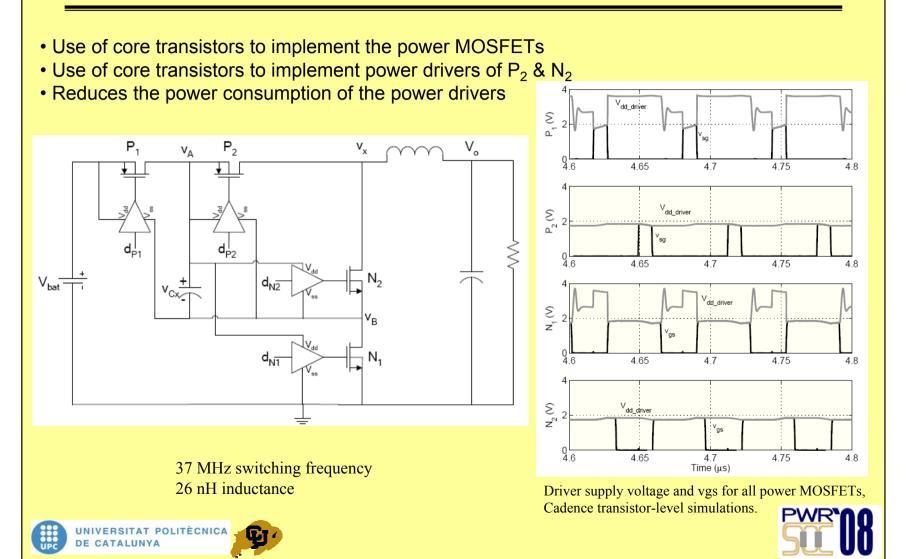
Self-driving scheme to interconnect power transistors and drivers, which reduces the voltage across the power MOSFETs gate dielectric.



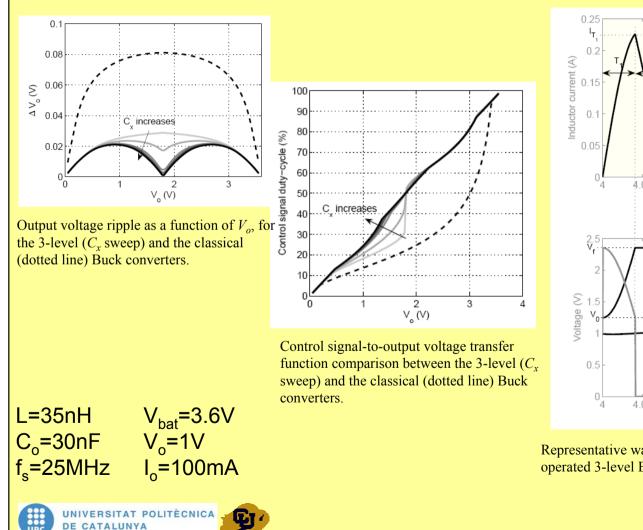


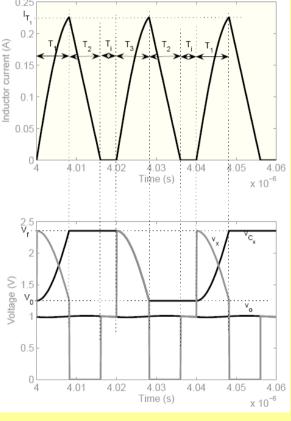


3-level self-driving PFM low-Cx buck converter



3-level self-driving PFM low-Cx buck converter





Representative waveforms corresponding to a DCM operated 3-level Buck converter, duty cycle below 50%



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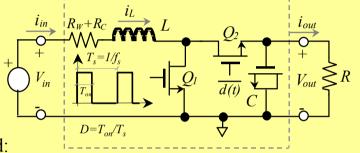


Circuit topology considerations

Optimized design space exploration (II)

1) Model each performance index (ripple, efficiency and area) as a function of design parameters: inductor, capacitor and switching frequency

A priori parameters and assumptions are application-oriented: topology, V_{in} , V_{out} , and the target IC technology parameters.



Output voltage ripple
$$\Delta v_o = \frac{V_o D T_s}{RC} = \frac{V_o D}{RCf_s} = f_{\Delta v_o}(L, C, f_s)$$

Efficiency
$$\eta = \frac{V_{in} I_L - P_{L-DC} - P_{L-core} - P_{Q-all}}{V_{in} I_L} = f_\eta(L, C, f_s)$$

Occupied area

$$Area = A_C + A_L + 2A_Q = f_{area}(L, C, f_s)$$





Circuit topology considerations

Optimized design space exploration (III)

area

2) Define a merit figure encompassing the performance indexes to be maximized or minimized

> generic merit figure $\Gamma(x_{1,\dots,}x_n) = \frac{\prod_i \beta_i f_i^{\gamma_i}(x_{1,\dots,}x_n)}{\prod_i \beta_j f_j^{\gamma_j}(x_{1,\dots,}x_n)}$

Boost converter case example merit figure

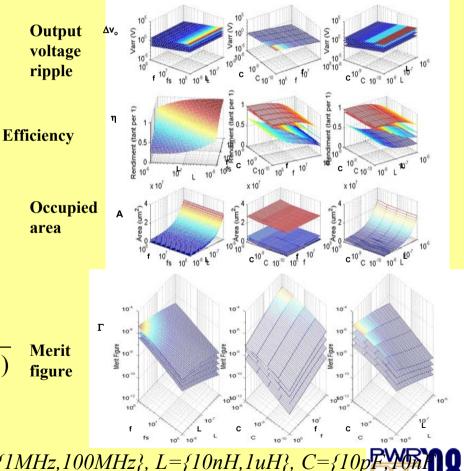
$$\Gamma(L,C,f_s) = \frac{f_{\eta}(L,C,f_s)}{f_A^2(L,C,f_s) \cdot f_{\Delta v_o}(L,C,f_s)} \quad \mathbf{M}_{\mathbf{fig}}$$

Note that the area dependence is square-weighted so as to solve the ill-conditioned solution of $\Delta vo \rightarrow \infty$ when $A \rightarrow 0$.



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 $f_{s} = \{1MHz, 100MHz\}, L = \{10nH, 1uH\}, C = \{10pF\}$

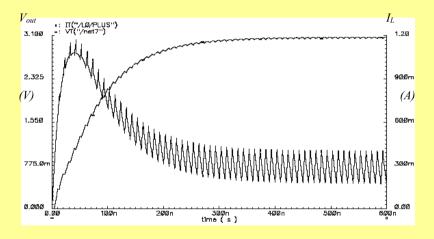


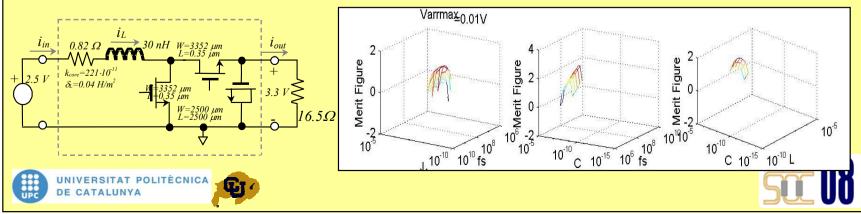
Circuit topology considerations

Optimized design space exploration (IV) Design example for a standard 0.35 µm CMOS technology

3) Obtain optimum point within **design space** (L,C,f_s) as regards **efficiency, occupied area, functionality**

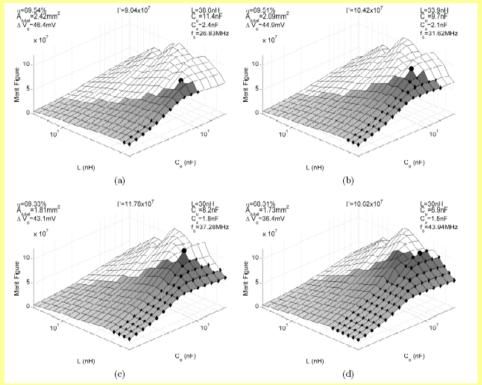
Specs: $\Delta_{vo} = 0.1 \ V \ i_{out} = 0.4 \ A$ **Optimization result:** $L = 30 \ nH, \ C = , f_s = 50 \ MHz$





Optimized design space exploration

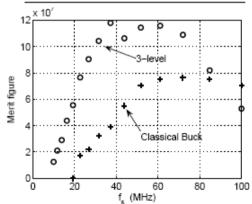
3-level converter design example for a standard 0.25 µm CMOS technology



Design space exploration of a CMOS-compatible 3-level converter: 70% efficiency, $5mm^2$ silicon and f_s =37 MHz

Table 6.3. 3-level converter selected design main characteristics, referred to $I_c = 100 \, mA$ $\hline 100 \, mA$ Inductor (L) 26.73 nH

Inductor (L)	26.73 nH
Output capacitor (C_o)	25.89 nF
C_x capacitor (C_x)	5.07 nF
Switching frequency (f_s)	37.28MHz
T_1 and T_3 duration	6.85 ns
T ₂ duration	5.65 ns
T'_1 and T'_3 inactivity states duration	917 ps
Operating mode	DCM
Inductor current at the end of $T_1(I_{T_1})$	211.2 mA
Total power losses (P_{losses})	43.5 mW
Power efficiency (η)	69.68%
Total occupied area (A_{total})	$5.09 mm^2$
Output voltage ripple $\rightarrow I_o = 100 mA (\Delta V_o)$	14.6 mV
Output voltage ripple $\rightarrow I_o = 5 mA (\Delta V_o)$	49.4 mV







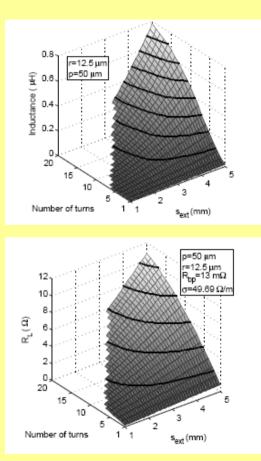
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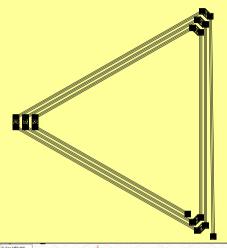
Bondwire triangular spiral inductors in standard CMOS

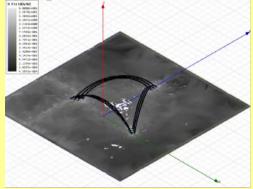


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Technical parameter Desired inductance Tolerance on desired value Bonding pad resistance R_{bp} Bonding wire resistivity ζ	Value 50 nH 3% $13 m\Omega$ $49.69 \Omega/m$ $12.5 \mu m$
Tolerance on desired value Bonding pad resistance R_{bp}	3% 13 <i>mΩ</i> 49.69Ω/m
Bonding pad resistance R_{bp}	$13 m \Omega$ $49.69 \Omega / m$
	$49.69 \Omega/m$
Bonding wire resistivity ζ	1
	$12.5 \mu m$
Bonding wire radius R	
Distance between bonding wires p	$50 \mu m$
Area coefficient γ_{LA}	1
Resistance coefficient γ_{LR}	10
Characteristic	Value
Final inductance L	48.95 nH
Outer side length s_{ext}	2.6mm
Number of turns n_L	4
Occupied area A_L	$3.02 mm^2$
ESR R_L	1.503Ω



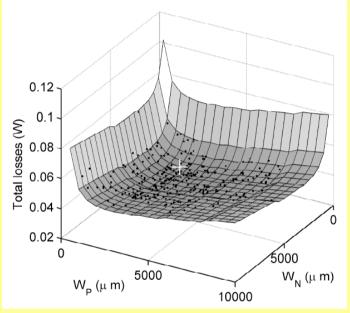


•Area underneath inductor is usable for capacitors and power MOSFETs

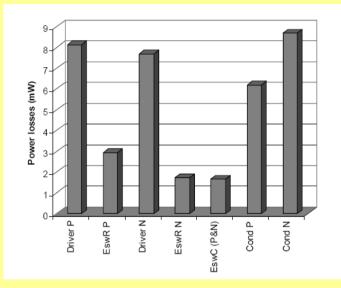


Power MOSFETs

Complete loss optimization of on-chip CMOS synchronous rectifier



 $W_P = 3092 \mu m$ $W_N = 2913 \mu m$ power drivers with 7.59 and 7.48 tapering factors Overall losses 37.1mW



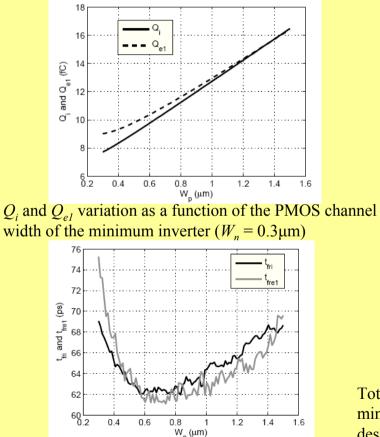
Breakdown of loss distribution, corresponding the optimized design of power MOSFETs and their associated drivers.





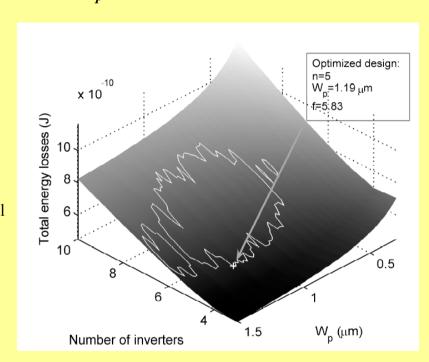
Power MOSFET gate drive design

Additional degree of freedom: impact of W_p upon efficiency and delay



 t_{fri} and t_{fre1} parameter variation

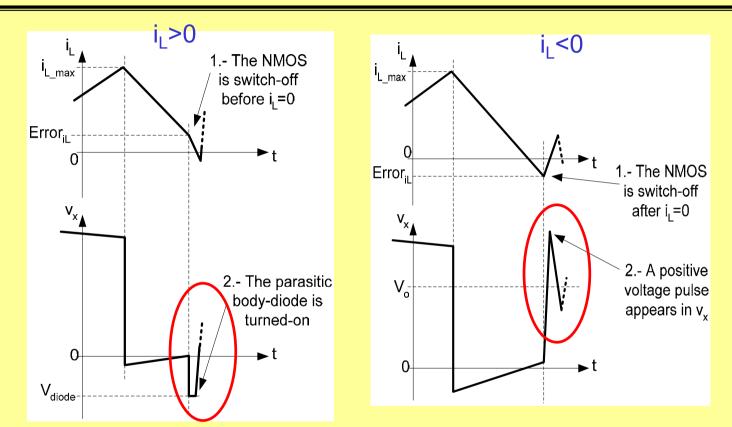




Total energy losses as a function of the number of inverters n and the minimum inverter PMOS channel width W_p . The area includes all the designs constrainted to a propagation delay lower than 1.15 ns.



iL=0 detection circuit. Event detection



The body diode of the NMOS power switch turns-on as a consequence of a premature cut off of the power transistor Inductor current charges the *x*-node parasitic capacitor and a positive voltage pulse appears in Vx voltage, due to late cut off of the power transistor

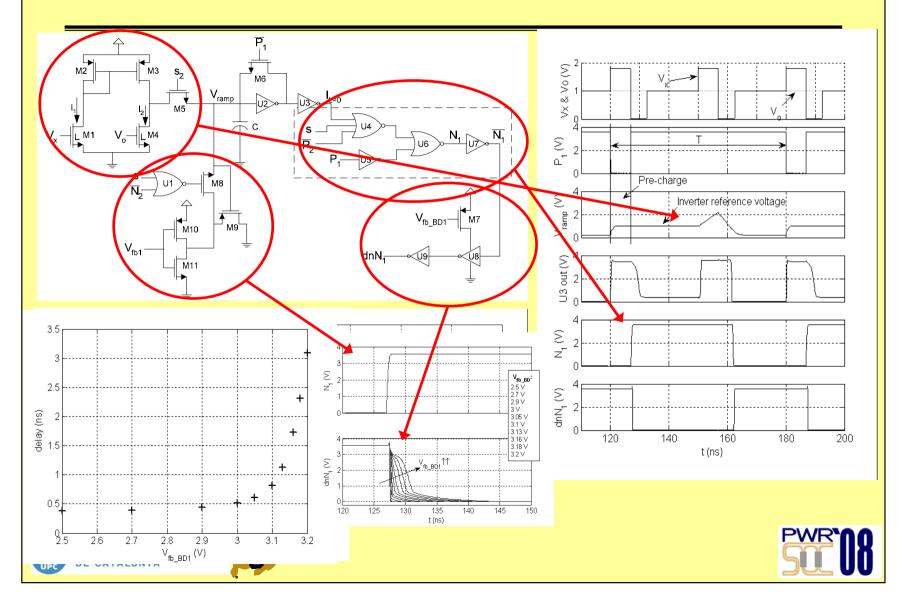


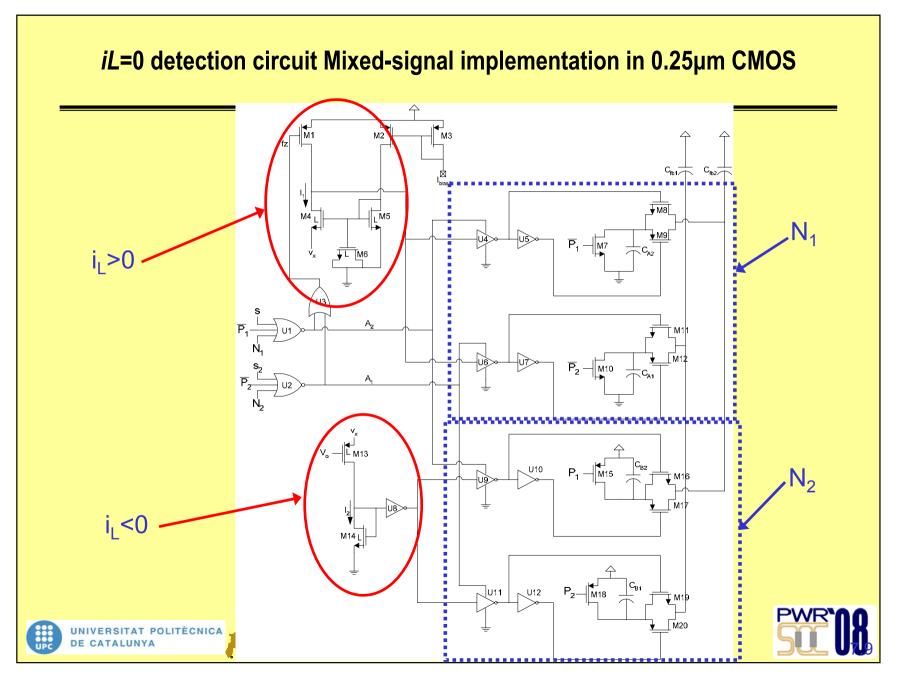


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iL=0 detection circuit. Circuit for time adjustment. Inductor current observer

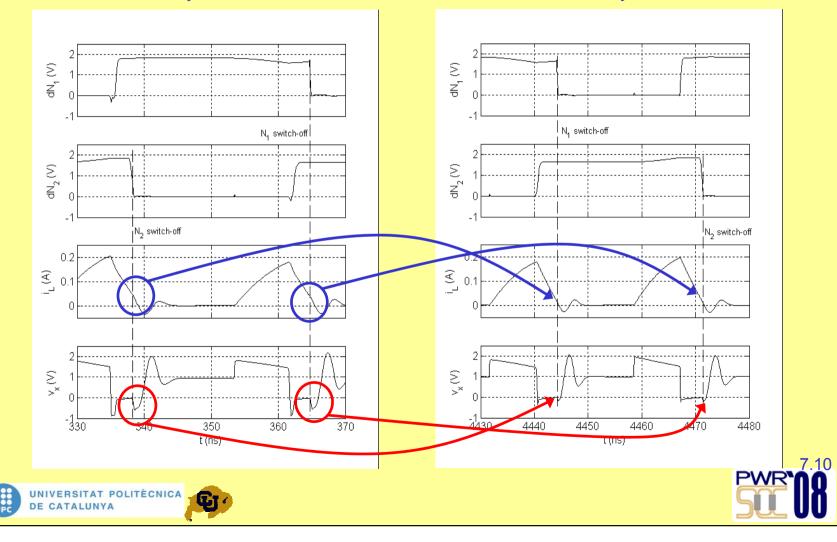




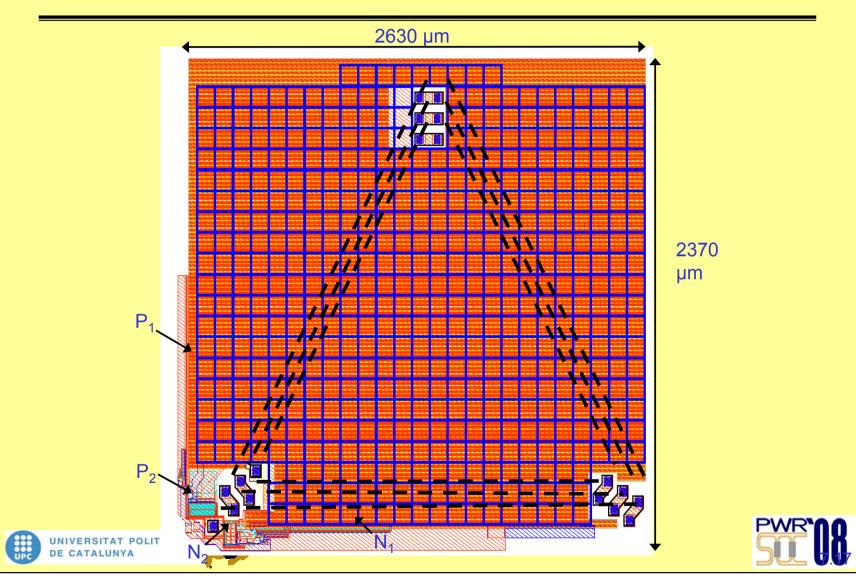
Time-domain performance of *iL*=0 detection circuit

Before adjustment

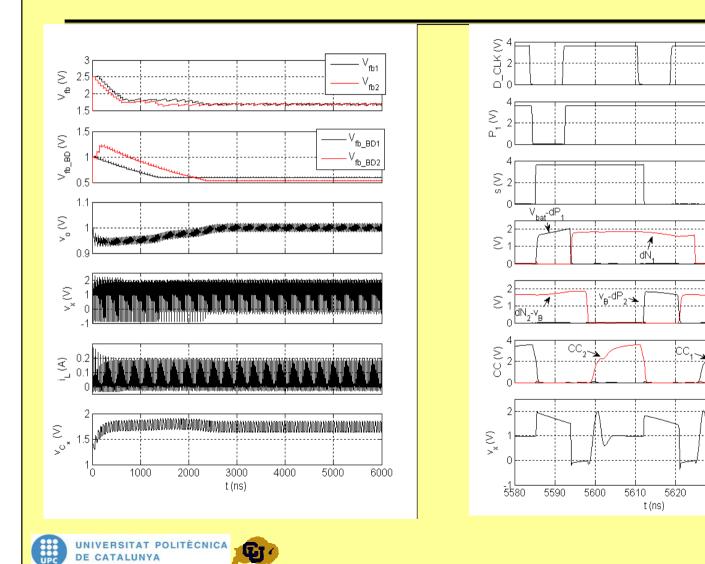
After *iL*=0 adjustment



Complete integrated 3-level CMOS switching power converter

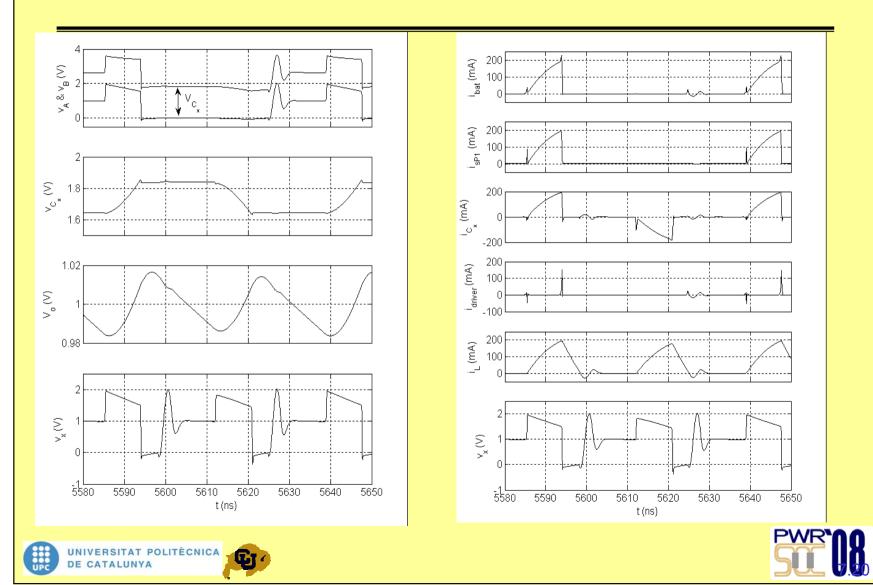


Full-transistor-level circuit results (I)

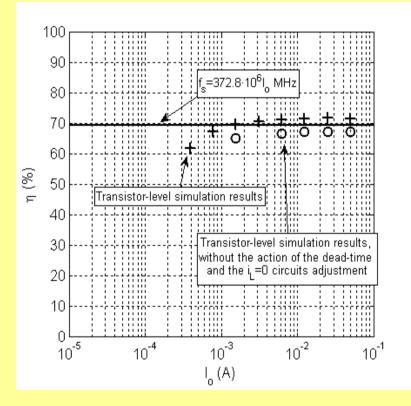


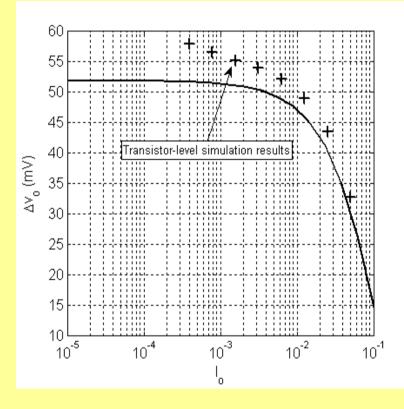


Full-transistor-level circuit results (II)



Full-transistor-level circuit results (III)



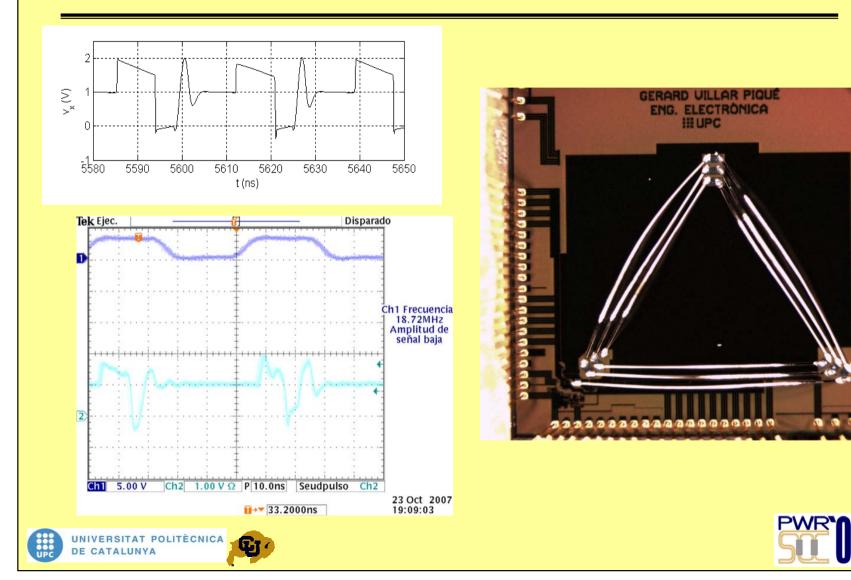






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Experimental results



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Conclusions

- Three-level converter results in favorable trade-offs in terms of decreasing the switching ripples, decreasing the switching frequency, reducing the size of the filter elements, increasing the converter open-loop bandwidth, or increasing the converter efficiency.
- The 3-level converter with low-Cx, self-biased drivers and operating in DCM/PFM has been presented as a candidate for DC-DC converter integration
- The use of the self-driving scheme to supply the drivers allows the use of thin-oxide transistors which increases the performance of the switches.
- Design optimization results in the 3-level converter outperforming the Buck converter.

Future research lines

- Linear-assisted scheme for multilevel converters
- Explore extending the approach to more intermediate levels
- Use different modulations (e.g. asynchronous sigma delta)
- Applying time optimal control



